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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	128KB (128K × 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f410rbt7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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### 2.1 Compatibility with STM32F4 series

The STM32F410x8/B are fully software and feature compatible with the STM32F4 series (STM32F42x, STM32F401, STM32F43x, STM32F41x, STM32F405 and STM32F407)

The STM32F410x8/B can be used as drop-in replacement of the other STM32F4 products but some slight changes have to be done on the PCB board.





1. For STM32F410xB devices, pin 54 is bonded to PB11 instead of PD2.



### 3 Functional overview

# 3.1 ARM<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU core with embedded Flash and SRAM

The ARM<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU 32-bit RISC processor features exceptional codeefficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices. The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution. Its single precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

The STM32F410x8/B devices are compatible with all ARM tools and software.

Figure 2 shows the general block diagram of the STM32F410x8/B.

Note: Cortex<sup>®</sup>-M4 with FPU is binary compatible with Cortex<sup>®</sup>-M3.

### 3.2 Adaptive real-time memory accelerator (ART Accelerator<sup>™</sup>)

The ART Accelerator<sup>™</sup> is a memory accelerator which is optimized for STM32 industrystandard ARM<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU processors. It balances the inherent performance advantage of the ARM<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor full 125 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART Accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 100 MHz.

### 3.3 Batch Acquisition mode (BAM)

The Batch acquisition mode allows enhanced power efficiency during data batching. It enables data acquisition through any communication peripherals directly to memory using the DMA in reduced power consumption as well as data processing while the rest of the system is in low-power mode (including the flash and ART). For example in an audio system, a smart combination of PDM audio sample acquisition and processing from the I2S directly to RAM (flash and ART<sup>TM</sup> stopped) with the DMA using BAM followed by some very short processing from flash allows to drastically reduce the power consumption of the application. A dedicated application note (AN4515) describes how to implement the STM32F410x8/B BAM to allow the best power efficiency.





and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The RTC and the low-power timer (LPTIM1) can remain active in Stop mode. They can consequently be used to wake up the device from this mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, LPTIM1, the RTC alarm/ wakeup/ tamper/ time stamp events).

#### • Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm/ wakeup/ tamper/time stamp event occurs.

Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

### 3.19 V<sub>BAT</sub> operation

The VBAT pin allows to power the device  $V_{BAT}$  domain from an external battery, an external super-capacitor, or from  $V_{DD}$  when no external battery and an external super-capacitor are present.

 $V_{BAT}$  operation is activated when  $V_{DD}$  is not present.

The VBAT pin supplies the RTC and the backup registers.

Note: When the microcontroller is supplied from VBAT, external interrupts and RTC alarm/events do not exit it from  $V_{BAT}$  operation. When PDR\_ON pin is not connected to  $V_{DD}$  (internal Reset OFF), the  $V_{BAT}$  functionality is no more available and VBAT pin should be connected to  $V_{DD}$ .

### 3.20 Timers and watchdogs

The devices embed one advanced-control timer, four general purpose timers, one low power timer, two watchdog timers and one SysTick timer.

All timer counters can be frozen in debug mode.

*Table 5* compares the features of the advanced-control and general-purpose timers.



USART name	Standard features	Modem (RTS/CTS)	LIN	SPI master	irDA	Smartcard (ISO 7816)	Max. baud rate in Mbit/s (oversampling by 16)	Max. baud rate in Mbit/s (oversampling by 8)	APB mapping
USART1	х	X <sup>(1)</sup>	x	х	х	х	6.25	12.5	APB2 (max. 100 MHz)
USART2	х	X <sup>(1)</sup>	x	X <sup>(1)</sup>	х	X <sup>(1)</sup>	3.12	6.25	APB1 (max. 50 MHz)
USART6 (1)	x	N.A	x	X <sup>(1)(2)</sup>	х	X <sup>(1)(2)</sup>	6.25	12.5	APB2 (max. 50 MHz)

 Table 7. USART feature comparison

1. Not available on WLCSP36 package.

2. Not available on UFQFPN48 package.

### 3.23 Serial peripheral interface (SPI)

The devices feature three SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1 and SPI5 can communicate at up to 50 Mbit/s, SPI2 can communicate at up to 25 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

### 3.24 Inter-integrated sound (I<sup>2</sup>S)

Three standard  $I^2S$  interfaces (multiplexed with SPI1 to SPI5) are available. They can be operated in master or slave mode, in simplex communication modes and can be configured to operate with a 16-/32-bit resolution as an input or output channel. All the I2Sx audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I<sup>2</sup>S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I<sup>2</sup>Sx can be served by the DMA controller.

### 3.25 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.



	Ρ	'in Num	nber				ē			
WLCSP36	LQFP48	UFQFPN48	LQFP64	UFBGA64	Pin name (function after reset) <sup>(1)</sup>	Pin type	Pin type I/O structu		Alternate functions	Additional functions
D1	29	29	41	C8	PA8	I/O	FT	-	MCO_1, TIM1_CH1, I2C4_SCL, USART1_CK, EVENTOUT	-
-	30	30	42	B8	PA9	I/O	FT	-	TIM1_CH2, USART1_TX, EVENTOUT	-
-	31	31	43	E6	PA10	I/O	FT	-	TIM1_CH3, SPI5_MOSI/I2S5_SD, USART1_RX, EVENTOUT	-
-	32	32	44	D7	PA11	I/O	FT	-	TIM1_CH4, USART1_CTS, USART6_TX, EVENTOUT	-
D2	33	33	45	A8	PA12	I/O	FT	-	TIM1_ETR, SPI5_MISO, USART1_RTS, USART6_RX, EVENTOUT	-
C1	34	34	46	C7	PA13	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
B1	35	35	47	D5	VSS	S	-	-	-	-
-	36	36	48	-	VDD	S	-	-	-	-
A1	-	-	-	-	VDD	S	-	-	-	-
B2	37	37	49	B7	PA14	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
A2	38	38	50	A7	PA15	I/O	FT	-	JTDI, SPI1_NSS/I2S1_WS, USART1_TX, EVENTOUT	-
-	-	-	51	C6	PC10	I/O	FT	-	TRACED0, TIM5_CH2, EVENTOUT	-
-	-	-	52	B6	PC11	I/O	FT	-	TRACED1, TIM5_CH3, EVENTOUT	-
-	-	-	53	A6	PC12	I/O	FT	-	TRACED2, TIM11_CH1, EVENTOUT	-

Table 9. STM32F410x8/B pin definitions (continued)



Symbol	Ratings	Max.	Unit	
$\Sigma I_{VDD}$	Total current into sum of all $V_{DD_x}$ power lines (source) <sup>(1)</sup>	160		
$\Sigma I_{VSS}$	Total current out of sum of all $V_{SS_x}$ ground lines $(sink)^{(1)}$	-160		
I <sub>VDD</sub>	Maximum current into each V <sub>DD_x</sub> power line (source) <sup>(1)</sup>	100		
I <sub>VSS</sub>	Maximum current out of each $V_{SS_x}$ ground line (sink) <sup>(1)</sup>	-100		
	Output current sunk by any I/O and control pin			
IIO	Output current sourced by any I/O and control pin	-25	mA	
ΣI	Total output current sunk by sum of all I/O and control pins <sup>(2)</sup>	120		
2110	Total output current sourced by sum of all I/Os and control pins <sup>(2)</sup>	-120		
(3)	(3) Injected current on FT and TC pins <sup>(4)</sup>			
INJ(PIN)	Injected current on NRST and B pins <sup>(4)</sup>			
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins) <sup>(5)</sup> ±25			

#### Table 13. Current characteristics

1. All main power ( $V_{DD}$ ,  $V_{DDA}$ ) and ground ( $V_{SS}$ ,  $V_{SSA}$ ) pins must always be connected to the external power supply, in the permitted range.

2. This current consumption must be correctly distributed over all I/Os and control pins.

3. Negative injection disturbs the analog performance of the device. See note in Section 6.3.20: 12-bit ADC characteristics.

4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.

5. When several inputs are submitted to a current injection, the maximum  $\Sigma I_{INJ(PIN)}$  is the absolute sum of the positive and negative injected currents (instantaneous values).

Symbol	Ratings	Value	Unit
T <sub>STG</sub>	Storage temperature range	–65 to +150	
TJ	Maximum junction temperature	130	
T <sub>LEAD</sub>	Maximum lead temperature during soldering (WLCSP36, LQFP48, LQFP64, UFQFPN48, UFBGA64)	see note <sup>(1)</sup>	°C

#### Table 14. Thermal characteristics

 Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK<sup>®</sup> 7191395 specification, and the European directive on Restrictions on Hazardous Substances (ROHS directive 2011/65/EU, July 2011).

### 6.3 Operating conditions

### 6.3.1 General operating conditions

Table 15.	General	operating	conditions
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit		
		Power Scale3: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x01	0	-	64			
fhclk	Internal AHB clock frequency	Power Scale2: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x10	0	-	84	MHz		
		Power Scale1: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x11	0	-	100			
f <sub>PCLK1</sub>	Internal APB1 clock frequency	-	0	-	50	MHz		
f <sub>PCLK2</sub>	Internal APB2 clock frequency	-	0	-	100	MHz		
V <sub>DD</sub>	Standard operating voltage	-	1.7 <sup>(1)</sup>	-	3.6	V		
V (2)(3)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as $V = \begin{pmatrix} 4 \end{pmatrix}$	1.7 <sup>(1)</sup>	-	2.4	N		
V <sub>DDA</sub> <sup>(2)(0)</sup> Analog operating voltage (ADC limited to 2.4 M samples)				-	3.6			
V <sub>BAT</sub>	Backup operating voltage	-	1.65	-	3.6	V		
		VOS[1:0] bits in PWR_CR register = 0x01 Max frequency 64 MHz	1.08 (5)	1.14	1.20 <sup>(5)</sup>			
V <sub>12</sub>	Regulator ON: 1.2 V internal voltage on VCAP_1 pins	Ilator ON: 1.2 V internalVOS[1:0] bits in PWR_CR register = 0x10ge on VCAP_1 pinsMax frequency 84 MHz		1.26	1.32 <sup>(5)</sup>	v		
		VOS[1:0] bits in PWR_CR register = 0x11 Max frequency 100 MHz	1.26	1.32	1.38			
	Regulator OFE <sup>,</sup> 1.2 V external	Max frequency 64 MHz	1.10	1.14	1.20			
V <sub>12</sub>	voltage must be supplied on	Max frequency 84 MHz	1.20	1.26	1.32	V		
	VCAP_1 pins	Max frequency 100 MHz	1.26	1.32	1.38	1		
	Input voltage on RST, FT and	$2 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	-0.3	-	5.5			
V <sub>IN</sub>	TC pins <sup>(6)</sup>	$V_{DD} \leq 2 V$	-0.3	-	5.2	V		
	Input voltage on BOOT0 pin	-	0	-	9			



				Valtaria	PLL	Тур		Max	x <sup>(2)</sup>		
Symbol P	Parameter	Conditions	<sup>T</sup> HCLK (MHz)	scale	(MHz) (1)	T <sub>A</sub> = 25 ℃	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	T <sub>A</sub> = 125 °C	Unit
			100	S1	200	16.3	17.3 <sup>(5)</sup>	17.1	17.5 <sup>(6)</sup>	18.4 <sup>(5)</sup>	
		Extornal	84	S2	168	13.2	14.1	14.0	14.3	15.2	
		clock,	64	S3	128	9.3	10.0	9.9	10.2	11.1	
		all peripherals $(3)(4)$	50	S3	100	7.4	8.0	8.0	8.3	9.2	
		enableu	25	S3	100	4.2	4.7	4.8	5.0	5.9	
			20	S3	160	3.7	4.2	4.3	4.6	5.5	
		HSI, PLL OFF, all peripherals enabled <sup>(3)(4)</sup>	16	S3	off	2.4	2.8	3.0	3.4	4.3	
:	Supply		1	S3	off	0.6	1.0	1.2	1.5	2.4	~
IDD	Run mode	External clock, all peripherals	100	S1	200	10.6	11.4 <sup>(5)</sup>	11.4	11.7 <sup>(6)</sup>	12.6 <sup>(5)</sup>	mA
			84	S2	168	8.7	9.4	9.3	9.7	10.6	
			64	S3	128	6.2	6.8	6.8	7.1	7.9	
			50	S3	100	5.0	5.5	5.5	5.8	6.8	
		uisableu	25	S3	100	2.9	3.4	3.5	3.8	4.7	
			20	S3	160	2.7	3.1	3.2	3.5	4.4	
		HSI, PLL	16	S3	off	1.7	2.1	2.3	2.6	3.5	
		OFF, all peripherals disabled <sup>(3)</sup>	1	S3	off	0.6	0.9	1.1	1.5	2.4	

## Table 24. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory - V<sub>DD</sub> = 3.6 V

1. Refer to *Table 44* and RM0401 for the possible PLL VCO setting

2. Guaranteed by characterization, unless otherwise specified.

3. When the ADC is ON (ADON bit set in ADC\_CR2), an additional power consumption of 1.6 mA must be added.

4. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC\_CR2 register)

5. Guaranteed by tests in production.

6. Guaranteed by test in production on temperature range 7 salestypes only.

trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

**Caution:** Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 36: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

 $I_{SW}$  is the current sunk by a switching I/O to charge/discharge the capacitive load  $V_{DD}$  is the MCU supply voltage

f<sub>SW</sub> is the I/O switching frequency

C is the total capacitance seen by the I/O pin: C =  $C_{INT}$ +  $C_{EXT}$ 

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSE_ext</sub>	External user clock source frequency <sup>(1)</sup>		1	-	50	MHz
V <sub>HSEH</sub>	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	$V_{DD}$	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage	-	$V_{SS}$	-	$0.3V_{\text{DD}}$	v
t <sub>w(HSE)</sub> t <sub>w(HSE)</sub>	OSC_IN high or low time <sup>(1)</sup>		5	-	-	ne
t <sub>r(HSE)</sub> t <sub>f(HSE)</sub>	OSC_IN rise or fall time <sup>(1)</sup>		-	-	10	115
C <sub>in(HSE)</sub>	OSC_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
١	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

Table 38. High-speed external user clock characteristics

1. Guaranteed by design.

#### Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the *Table 55*. However, the recommended clock input waveform is shown in *Figure 20*.

The characteristics given in *Table 39* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 15*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSE_ext</sub>	User External clock source frequency <sup>(1)</sup>		-	32.768	1000	kHz
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	-	V <sub>SS</sub>	-	0.3V <sub>DD</sub>	
t <sub>w(LSE)</sub> t <sub>f(LSE)</sub>	OSC32_IN high or low time <sup>(1)</sup>		450	-	-	ns
t <sub>r(LSE)</sub> t <sub>f(LSE)</sub>	OSC32_IN rise or fall time <sup>(1)</sup>		-	-	50	113
C <sub>in(LSE)</sub>	OSC32_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
DuCy <sub>(LSE)</sub>	Duty cycle	-	30	-	70	%
١L	OSC32_IN Input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$	-	-	±1	μA

Table 39. Low-speed e	external user clock characteristics
-----------------------	-------------------------------------

1. Guaranteed by design.



#### 6.3.9 Internal clock source characteristics

The parameters given in *Table 42* and *Table 43* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 15*.

#### High-speed internal (HSI) RC oscillator

Symbol	Parameter	С	Min	Тур	Max	Unit	
f <sub>HSI</sub>	Frequency	-		-	16	-	MHz
		User-trimmed register <sup>(2)</sup>	with the RCC_CR	-	-	1	%
ACC <sub>HSI</sub> A	Accuracy of the HSI oscillator	Factory- calibrated	$T_A = -40$ to 125 °C <sup>(3)</sup>	-8	-	5.5	%
			$T_A = -10$ to 85 °C <sup>(3)</sup>	-4	-	4	%
			$T_A = 25 \ ^{\circ}C^{(4)}$	–1	-	1	%
t <sub>su(HSI)</sub> <sup>(2)</sup>	HSI oscillator startup time	-		-	2.2	4	μs
I <sub>DD(HSI)</sub> <sup>(2)</sup>	HSI oscillator power consumption	-		-	60	80	μA

Table 42	цеі	occillator	aharaa	toriotion	(1)
Table 42.	HSI	oscillator	cnarac	teristics	··/

1. V<sub>DD</sub> = 3.3 V, T<sub>A</sub> = –40 to 125 °C unless otherwise specified.

2. Guaranteed by design.

3. Guaranteed by characterization.

4. Factory calibrated non-soldered parts.





<sup>1.</sup> Guaranteed by characterization.





Figure 29. Recommended NRST pin protection

1. The reset network protects the device against parasitic resets.

 The user must ensure that the level on the NRST pin can go below the V<sub>IL(NRST)</sub> max level specified in Table 58. Otherwise the reset is not taken into account by the device.

#### 6.3.18 TIM timer characteristics

The parameters given in Table 59 are guaranteed by design.

Refer to Section 6.3.16: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions <sup>(3)</sup>	Min	Max	Unit
		AHB/APBx	1	-	t <sub>TIMxCLK</sub>
t <sub>res(TIM)</sub>	Timer resolution time	prescaler=1 or 2 or 4, f <sub>TIMxCLK</sub> = 100 MHz	11.9	-	ns
		AHB/APBx	1	-	t <sub>TIMxCLK</sub>
		prescaler>4, f <sub>TIMxCLK</sub> = 100 MHz	11.9	-	ns
Timer external clock			0	f <sub>TIMxCLK</sub> /2	MHz
† <sub>EXT</sub>	CH4	f <sub>TIMxCLK</sub> = 100 MHz	0	50	MHz
Res <sub>TIM</sub>	Timer resolution		-	16/32	bit
t <sub>COUNTER</sub>	16-bit counter clock period when internal clock is selected	f <sub>TIMxCLK</sub> = 100 MHz	0.0119	780	μs
t <sub>MAX COUNT</sub>	Maximum possible count	-	-	65536 × 65536	t <sub>TIMxCLK</sub>
_		f <sub>TIMxCLK</sub> = 100 MHz	-	51.1	S

Table 59. TIMx characteristics<sup>(1)(2)</sup>

1. TIMx is used as a general term to refer to the TIM1 to TIM11 timers.

2. Guaranteed by design.

 The maximum timer frequency on APB1 is 50 MHz and on APB2 is up to 100 MHz, by setting the TIMPRE bit in the RCC\_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then TIMxCLK = HCKL, otherwise TIMxCLK >= 4x PCLKx.



f. (kH=)	I2C_CCR value		
	R <sub>P</sub> = 4.7 kΩ		
400	0x8019		
300	0x8021		
200	0x8032		
100	0x0096		
50	0x012C		
20	0x02EE		

Table 62 SCI	frequency	$(f_{\text{DO}})_{\text{CO}} = 42$	MH7 V = V	$x_{2} = 3 3 V^{(1)(2)}$
Table 62. SCL	irequency	(IPC K1 = 42)	IVIFIZ., V = 0	$12C = 3.3 V$ ( $^{12}C$

1.  $R_P$  = External pull-up resistance,  $f_{SCL} = I^2C$  speed,

For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed ±2%. These variations depend on the accuracy of the external components used to design the application.





Figure 33. SPI timing diagram - slave mode and CPHA =  $1^{(1)}$ 







Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Any positive injection current within the limits specified for  $I_{INJ(PIN)}$  and  $\Sigma I_{INJ(PIN)}$  in Section 6.3.16 does not affect the ADC accuracy.





- 1. See also Table 68.
- 2. Example of an actual transfer curve.
- 3. Ideal transfer curve.
- 4. End point correlation line.
- 5. E<sub>T</sub> = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves. EO = Offset Error: deviation between the first actual transition and the first ideal one. EG = Gain Error: deviation between the last ideal transition and the last actual one. ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one. EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.





Symbol	Parameter	Conditions	Min	Тур	Мах	, Unit	Comments
I <sub>DDA</sub> <sup>(4)</sup> DAC DC VDDA current consumption in quiescent mode <sup>(3)</sup>	-	-	280	380	μA	With no load, middle code (0x800) on the inputs	
	current consumption in quiescent mode <sup>(3)</sup>	-	-	475	625	μA	With no load, worst code $(0xF1C)$ at $V_{REF+} = 3.6$ V in terms of DC consumption on the inputs
Differential non linearity Differe	Differential non linearity Difference between two	-	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration.
	consecutive code- 1LSB)	-	-	-	±2	LSB	Given for the DAC in 12-bit configuration.
	Integral non linearity (difference	-	-	-	±1	LSB	Given for the DAC in 10-bit configuration.
INL <sup>(4)</sup> INL <sup>(4)</sup> ine drawn between Co a line drawn between Co and last Co 1023)	between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	-	±4	LSB	Given for the DAC in 12-bit configuration.
Offset <sup>(4)</sup> Offset <sup>(4)</sup> Co the V <sub>F</sub>	Offset error (difference between measured value at Code (0x800) and the ideal value = V <sub>REF+</sub> /2)	-	-	-	±10	mV	Given for the DAC in 12-bit configuration
		-	-	-	±3	LSB	Given for the DAC in 10-bit at $V_{REF+}$ = 3.6 V
		-	-	-	±12	LSB	Given for the DAC in 12-bit at $V_{REF+}$ = 3.6 V
Gain error <sup>(4)</sup>	Gain error	-	-	-	±0.5	%	Given for the DAC in 12-bit configuration
	Total Harmonic Distortion Buffer ON	-	-	3	6	μs	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$
THD <sup>(4)</sup>	-	-	-	-	-	dB	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$
Update rate <sup>(2)</sup>	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	-	1	MS/ s	$C_{LOAD}$ ≤ 50 pF, R <sub>LOAD</sub> ≥ 5 kΩ

Table 77. DAC characteristics (continued)



Dimension	Recommended values
Pitch	0.4 mm
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm

 Table 80. WLCSP36 recommended PCB design rules (0.4 mm pitch)

#### WLCSP36 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.



Figure 43. WLCSP36 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



#### **UFQFPN48** device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.



#### Figure 46. UFQFPN48 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



#### LQFP48 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

